

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND
PROGRAM

ABSTRACT

A technique includes a supply process including: (a0) supplying a process gas into a process chamber in which a substrate including a recess on a surface of the substrate is placed; (a1) increasing an internal pressure of the process chamber at least partially simultaneously with (a0); (a2) decreasing the internal pressure of the process chamber; and (b) supplying a dilution gas into the process chamber or increasing a flow rate of the dilution gas supplied into the process chamber, the supply process being performed so that the internal pressure of the process chamber reaches one or more local maximum values; and an exhaust process of exhausting an interior of the process chamber during at least a portion of the supply process, wherein, in the supply process, (b) is started before (a2) ends for a first time.

Fig. 4